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   Pary Baluswamy, Micron Technology, Inc. (United States)

10 Optical/DFM: Joint Session with Conference 8327
    Will Conley, Dynamic Intelligence (United States)
    Mark E. Mason, Texas Instruments Inc. (United States)
11 Joint Session with Conference 8327
John L. Sturtevant, Mentor Graphics Corporation (United States)
Kafai Lai, IBM Corporation (United States)

12 OPC
Bruce W. Smith, Rochester Institute of Technology (United States)
Kazuhiro Takahashi, Canon Inc. (Japan)

13 Tools
Soichi Owa, Nikon Corporation (Japan)
Kafai Lai, IBM Corporation (United States)

Poster Session
Peter D. Buck, Toppan Photomasks, Inc. (United States)
Geert Vandenberghe, IMEC (Belgium)